

IN THE CLAIMS

1-10. (Cancelled)

11. (Original) A method for manufacturing a reflective liquid crystal display device, the method comprising:

intersecting a plurality of gate lines and data lines on a first substrate;

forming a thin film transistor on the intersection of the gate line and the data line, the thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

forming a capacitor lower electrode of a storage capacitor on the same plane as the gate line;

forming an insulation film on the capacitor lower electrode;

forming an capacitor upper electrode on an upper portion of the capacitor lower electrode, the capacitor upper electrode being formed integrally with the drain electrode; and

forming a reflective electrode connected with the drain electrode.

12. (Original) A method for manufacturing a transflective liquid crystal display device, which has pixel areas defined into a reflection part and a transmission part, the method comprising:

intersecting a plurality of gate lines and data lines on a first substrate;

forming a thin film transistor on the intersection of the gate line and the data line, the thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

forming a capacitor lower electrode of a storage capacitor on the same plane as the gate line;

forming an insulation film on the capacitor lower electrode;

forming a capacitor upper electrode on an upper portion of the capacitor lower electrode, the capacitor upper electrode being formed integrally with the drain electrode;

forming a reflective electrode connected with the drain electrode at the reflection area;

and

forming a transfective electrode connected with the reflective electrode at the transmission area.

13. (New) The method for manufacturing of claim 11, wherein the insulation film is formed of one of silicone nitride (SiNx) and silicone oxide (SiOx).

14. (New) The method for manufacturing of claim 11, further comprising forming a passivation layer between the capacitor upper electrode and the reflective electrode.

15. (New) The method for manufacturing of claim 14, wherein the passivation layer is one of silicone nitride (SiNx), BCB and acryl resin.

16. (New) The method for manufacturing of claim 12, wherein the capacitor upper electrode extends along a boundary part between the reflective electrode and the transmissive electrode to prevent light leakage.

17. (New) The method for manufacturing of claim 12, wherein the insulation film is formed of one of silicone nitride (SiNx) and silicone oxide (SiOx)

18. (New) The method for manufacturing of claim 12, further comprising forming a passivation layer between the capacitor upper electrode and the reflective electrode.

19. (New) The method for manufacturing of claim 18, wherein the passivation layer is one of silicone nitride (SiNx), BCB and acryl resin.

20. (New) The method for manufacturing of claim 12, further comprising forming a another insulation layer between the reflective electrode and the transmissive electrode.